

### Synchronous Rectification Switcher Supporting CCM

## 1. Description

The MK1203 is a compact secondary side synchronous rectification switcher which integrated controller and MOSFET for high performance flyback converters. It is compatible with CCM, DCM and QR operations.

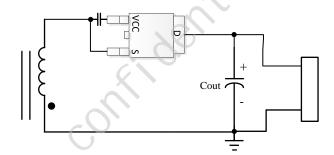
The MK1203 can generate its own supply voltage with high-side rectification, which eliminates the need of auxiliary winding of the transformer, usually required to produce supply voltage.

The extremely low 10ns turn-off propagation delay time and high sink current (~4A) capability of the driver improve SR VDS stress at CCM mode.

### 2. Typical Applications

- AC/DC Adapters for Mobile Phone and Notebook
- High Power density AC/DC Power Supplies
- Battery Powered System

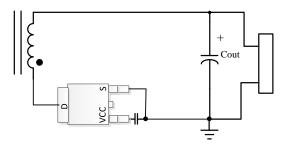
# 4. Simplified Application



Used in high side rectification

#### 3. Features

- Integrated 14mΩ 100V Power MOSFET
- Operates in a wide output voltage range down to 3V voltage (self-supply)
- Self-supply for operations with low-side rectification and high-side rectification without an auxiliary winding
- 10ns Fast Turn-off and 25ns Turn-on Delay
- VG Clamping Circuit Works Well when VCC is Below 2V
- Supports CCM, DCM and QR Operations
- Precise 0V turn off for maximum efficiency
- Designed for <200kHz working frequency</li>
- Available in TO-252 Package



Used in low side rectification



## 5. Ordering Information

Ordering No. <sup>(1)</sup>	Description	Material
MK1203CTB	TO-252, MSL-3, 2500 pcs/reel	Halogen free

### 6. Package Reference



XXXXXXXX: Lot code

MK1203CTB TO-252

Absolute Maximum Ratings (1)	Absolute	Maximum	Ratings	(1)
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VCC to S0.3V to	+20V
D to S0.7V to	100V
Continuous drain current I <sub>D</sub>	.7.5A <sup>(2)</sup>
Pulsed drain current I <sub>DM</sub>	30A <sup>(3)</sup>
Continuous Power Dissipation2.5W ( $T_A = +2$ )	5°C) (4)
Junction Temperature	150°C

# **Recommended Operation Conditions**VCC to S......5V to 9.5V

D to S.....-0.7V to 90V Maximum Junction Temp. (T<sub>J</sub>)......+125°C

Thermal Resistance  $^{(5)}$   $\theta_{JA}$   $\theta_{JC}$ 

TO-252...... 62 2.5 °C/W

#### Notes:

- (1) Exceeding these ratings may damage the device.
- (3) Repetitive rating: pulse width limited by maximum junction temperature
- (4) The maximum allowable power dissipation is a function of the maximum junction temperature T<sub>J</sub>(MAX), the junction-to-ambient thermal resistance θ<sub>JA</sub>, and the ambient temperature T<sub>A</sub>. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P<sub>D</sub>(MAX)=(T<sub>J</sub>(MAX)-T<sub>A</sub>)/θ<sub>JA</sub>. Exceeding the maximum allowable power dissipation will cause excessive die temperature.
- (5) Measured on JESDSD51-7, 4 layers PCB



## 7. Electrical Characteristics

T<sub>A</sub>=25°C, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Internal Mos Section						
Internal MOS Rdson	Rdson	Vcc=9.5V, Id=1A		14		mΩ
Drain to Source Breakdown	V <sub>DSS(BR)</sub>	Vcc=9.5V, Id=2mA	100			V
Supply Management Section						
VCC UVLO Rising	Vcc_on		4.3	4.6	4.9	V
VCC UVLO Falling	Vcc_off		3.8	4	4.3	VV
VCC UVLO Hysteresis	Vcc_hyst		0.25	0.6	0.75	V
VCC Regulation Voltage	V <sub>CC_REG</sub>	V <sub>D</sub> = 14V	8.2	9.1	10	V
Operating Current	Icc <sup>(6)</sup>	Vcc=6V, Fsw=100kHz,	1.5	2.0	2.5	mA
Quiescent Current	I <sub>q(VCC)</sub>	V <sub>CC</sub> =6.4V, Fsw=0Hz		350	550	μA
Mosfet Voltage Sensing						•
V <sub>D</sub> –V <sub>SS</sub> Adjusting Voltage	$V_{DS\_REG}$		-55	-40	-25	mV
Turn-On Threshold (V <sub>D</sub> -V <sub>SS</sub> )	$V_{ON\_th}$		-350	-300	-50	mV
Turn Off Threshold (V <sub>D</sub> -V <sub>SS</sub> )	$V_{OFF\_th}$	(0		0	10	mV
Turn-On Propagation Delay	$T_{D\_on}$	0)		25	40	ns
Turn-Off Propagation Delay	$T_{D\_off}$			10	15	ns
Turn On Blanking Time	T <sub>B_ON</sub>	$C_{LOAD} = 2.2nF$	0.75	1.0	1.3	μs
Turn Off Blanking V <sub>DS</sub> Threshold	$V_{B\_OFF}$			2		V
in T <sub>B_ON</sub>	<b>T</b>	O	250	200	350	
Turn Off Blanking Time  Gate Driver	Toff		250	300	350	ns
Gate Driver				1	1	
V <sub>G</sub> (Low)	$V_{G\_LOW}$	VCC=6.4V,	0	0.2	0.4	V
	, . <u> </u>	I <sub>LOAD</sub> =0.1A				
V <sub>G</sub> (High)	$V_{G\_HIGH}$	Vcc=6.4V,	Vcc-	Vcc-	Vcc	V
	0_111011	I <sub>LOAD</sub> =0.1A	0.6	0.3		-

#### Note:

## 8. Pin Functions

Pin #	Name	Description		
1	VCC	Inner Regulator Output, supply MK1203		
2	D	FET drain		
3	S	Ground		

<sup>(1)</sup> ICC in the table is the current consumed by the internal controller when 2.2nF load capacitance and 100kHz operating frequency.



# 9. Block Diagram

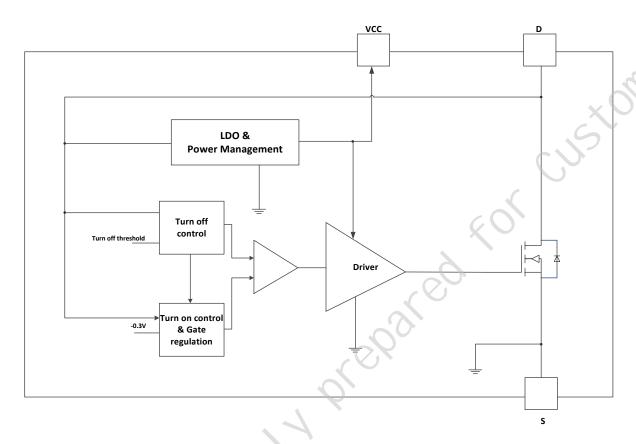


Figure 1. Functional Block Diagram



#### 10. Operation Descriptions

MK1203 is a high-performance synchronous rectifier which can replace the Schottky diode rectification in the flyback converter to improve efficiency, and support DCM, CCM and QR operations. A great flexibility for system design is brought by self-supply which supports operations with both low-side rectification and high-side rectification without an auxiliary winding.

#### 10.1. Conduction Phase

After SR VG turns on, a minimum blanking time  $T_{B\_ON}$  is required to prevent the parasitic ringing from falsely turning off SR VG. The minimum turn-on blanking time is around 1.0us for MK1203, during which the turn off threshold is increased to 2V. Right before  $T_{B\_ON}$  timer expires, MK1203 starts monitoring  $V_{DS}$  against a -40mV value to determine if internal VG needs to be slowly discharged. This operation adjusts  $V_{DS}$  of SR MOSFET to be around -40mV until the current through SR MOSFET drops to zero.

#### 10.2. Turn Off Phase

MK1203's turn-off threshold is different at different time. Within the minimum turn-on blanking time TB\_ON, VDS turn-off threshold is 2V which is the same as VB\_OFF. After the minimum turn-on blanking time TB\_ON, the turn-off threshold is around 0V, that combines with extremely fast 10ns turn-off propagation delay and 4A VG pull-down (sinking) current, synchronous rectifier is able to be turned off not too early which causes more SR FET body diode conduction time and more negative turn-off ringing, or not too late which creates risk of shoot through between primary side and SR side.



## 11. Typical Implementations

MK1203 supports both high side rectification and low side rectification to replace Schottky diode without the need of auxiliary winding as shown in Figure 2 and Figure 3. VCC is powered from pin VD and regulated at ~9V even when Vout is much lower than 5V. A 0.1uF bypass capacitor is suggested to regulate the bias voltage and reduce noise coupling from switching.

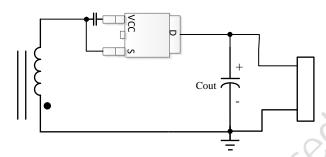


Figure 2. The High side rectification

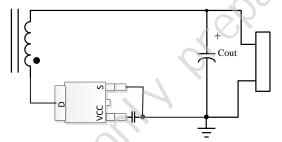
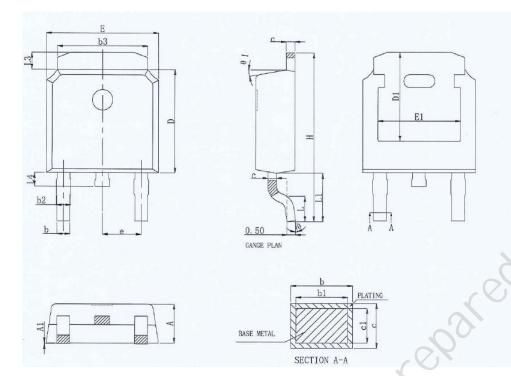


Figure 3. The low side rectification



# 12. Package Information (TO-252)



SYMBOL	MIN	NOM	MAX		
A	2. 20	2.30	2.40		
A1	0.00	-	0.12		
b	0.65	-	0.89		
b1	0.64	0.76	0.79		
b2	0.76	0.86	1.10		
b3	5. 20	5. 33	5. 46		
С	0.48	Col	0.60		
c1	0.47	0.51	0.55		
D	6.00	6.10	6. 20		
D1	5. 21		-		
Е	6.50	6.60	6. 70		
E1	4. 32	-	-		
e	2. 29BSC				
H	9.70	9. 95	10. 20		
L	1.40	1.50	1.60		
L1	2. 84REF				
L3	0.90	-	1.27		
L4	0.60	0.80	1.00		
θ	0°	-	10°		
θ 1	0°	_	15°		

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